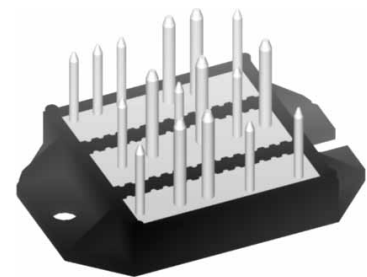
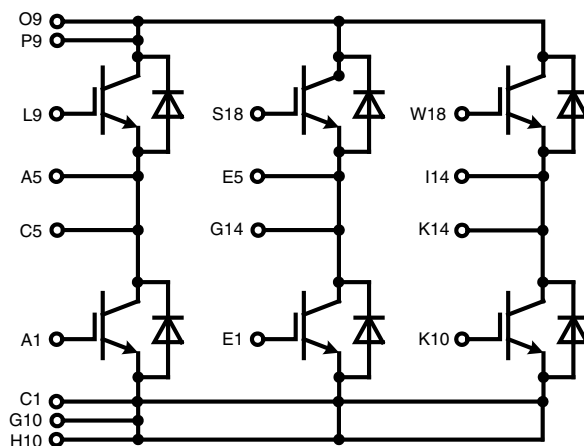


## Six-Pack XPT IGBT

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 28 \text{ A} \\ V_{CE(sat)} &= 2.1 \text{ V} \end{aligned}$$

**Part name** (Marking on product)

MIXA20W1200MC



### Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - square RBSOA @ 3x  $I_C$
  - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low  $V_{CE(sat)}$
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

### Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

### Package:

- "ECO-PAC2" standard package
- Easy to mount with two screws
- Insulated base plate
- Soldering pins for PCB mounting
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

## Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
$V_{CES}$	collector emitter voltage				1200	V	
$V_{GES}$	max. DC gate voltage	continuous			±20	V	
$V_{GEM}$	max. transient collector gate voltage	transient			±30	V	
$I_{C25}$	collector current		$T_C = 25^\circ\text{C}$		28	A	
$I_{C80}$			$T_C = 80^\circ\text{C}$		20	A	
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		100	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 16\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.8 2.1	2.1	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^\circ\text{C}$	5.5	6.0	6.5	V
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.02 0.2	0.2	mA mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$		47		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 56\ \Omega$	$T_{VJ} = 125^\circ\text{C}$	70		ns	
$t_r$	current rise time			40		ns	
$t_{d(off)}$	turn-off delay time			250		ns	
$t_f$	current fall time			100		ns	
$E_{on}$	turn-on energy per pulse			1.55		mJ	
$E_{off}$	turn-off energy per pulse			1.7		mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 56\ \Omega;$	$T_{VJ} = 125^\circ\text{C}$ $V_{CEK} = 1200\text{ V}$		45	A	
<b>SCSOA</b>	short circuit safe operating area		$T_{VJ} = 125^\circ\text{C}$		10	$\mu\text{s}$	
$t_{SC}$	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$					
$I_{SC}$	short circuit current	$R_G = 56\ \Omega; \text{non-repetitive}$		60		A	
$R_{thJC}$	thermal resistance junction to case	(per IGBT)			1.3	K/W	

## Output Inverter D1 - D6

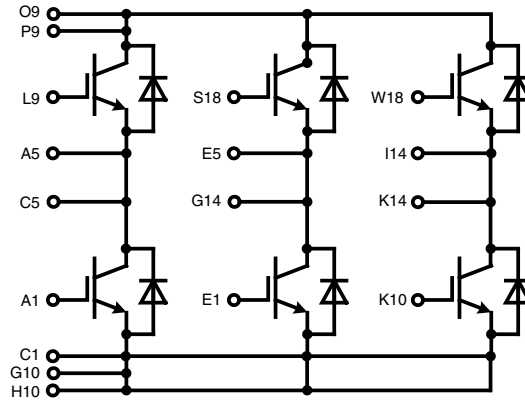
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_{RRM}$	max. repetitive reverse voltage		$T_{VJ} = 25^\circ\text{C}$		1200	V
$I_{F25}$	forward current		$T_C = 25^\circ\text{C}$		33	A
$I_{F80}$			$T_C = 80^\circ\text{C}$		22	A
$V_F$	forward voltage	$I_F = 20\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$	1.95 1.85	2.2	V V
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 20\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^\circ\text{C}$	3		$\mu\text{C}$
$I_{RM}$	max. reverse recovery current			20		A
$t_{rr}$	reverse recovery time			350		ns
$E_{rec}$	reverse recovery energy			0.7		mJ
$R_{thJC}$	thermal resistance junction to case	(per diode)			1.5	K/W

 $T_C = 25^\circ\text{C}$  unless otherwise stated

## Module

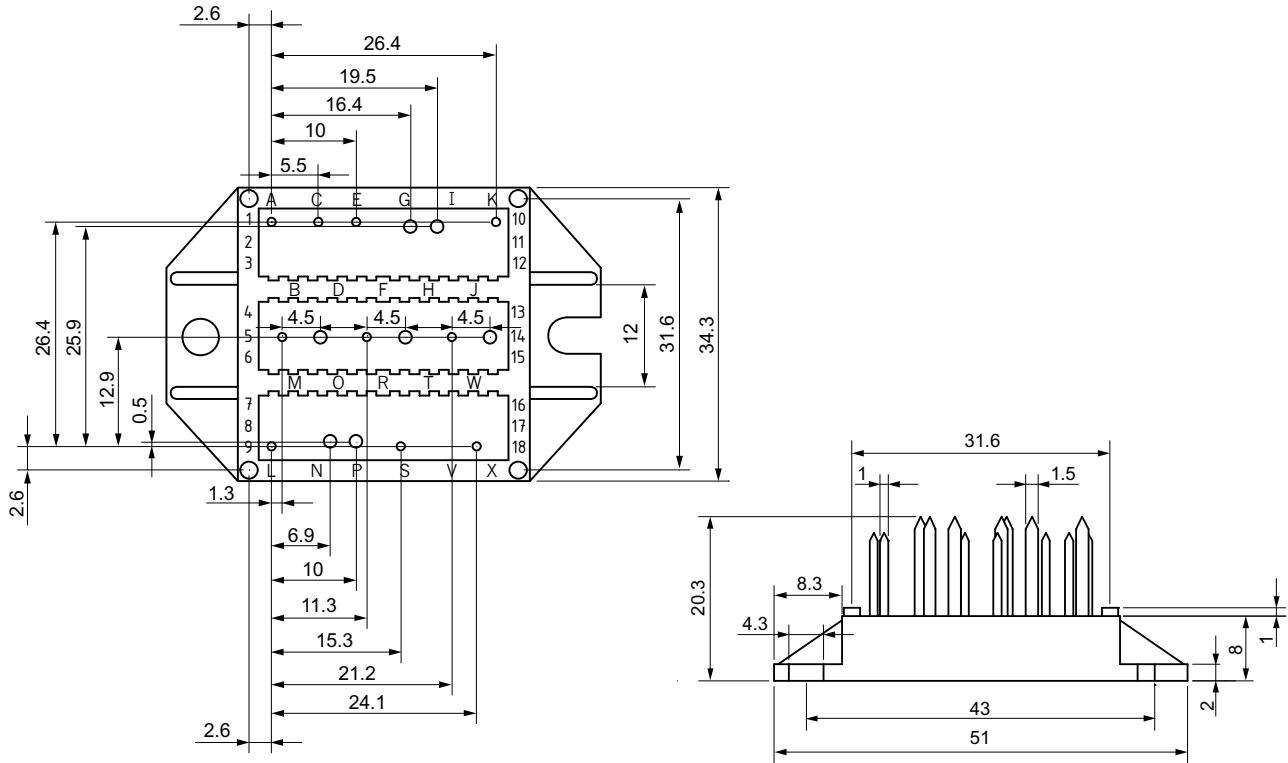
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$T_{VJ}$	<i>operating temperature</i>		-40		125	°C
$T_{VJM}$	<i>max. virtual junction temperature</i>				150	°C
$T_{stg}$	<i>storage temperature</i>		-40		125	°C
$V_{ISOL}$	<i>isolation voltage</i>	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}; t = 1 \text{ s}$			3600	V~
$M_d$	<i>mounting torque (M5)</i>		1.5		2	Nm
$d_s$	<i>creep distance on surface</i>		11.2			mm
$d_A$	<i>strike distance through air</i>		11.2			mm
<b>Weight</b>				24		g

### Circuit Diagram

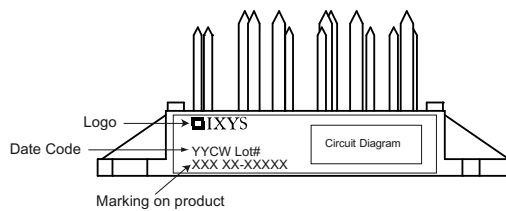


### Outline Drawing

Dimensions in mm (1 mm = 0.0394")



### Product Marking



#### Part number

- M = Module
- I = IGBT
- X = XPT
- A = Standard
- 20 = Current Rating [A]
- W = Six-Pack
- 1200 = Reverse Voltage [V]
- MC = ECO-PAC2

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA20W1200MC	MIXA20W1200MC	Box	6	509537

IXYS reserves the right to change limits, test conditions and dimensions.

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## Inverter T1 - T6

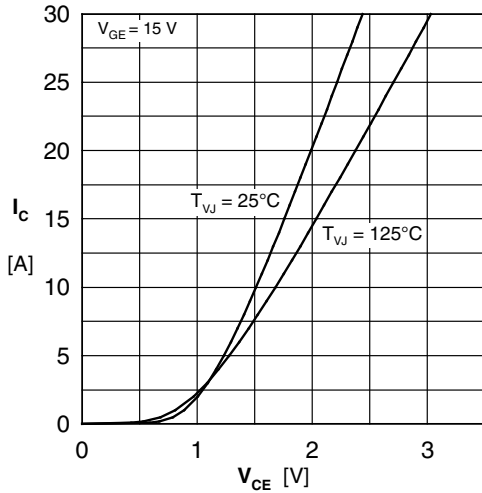


Fig. 1 Typ. output characteristics

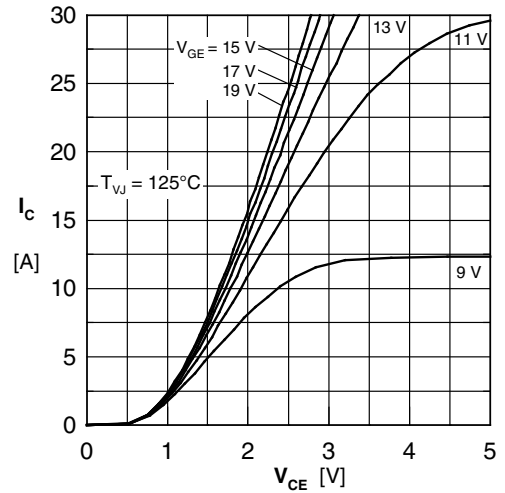


Fig. 2 Typ. output characteristics

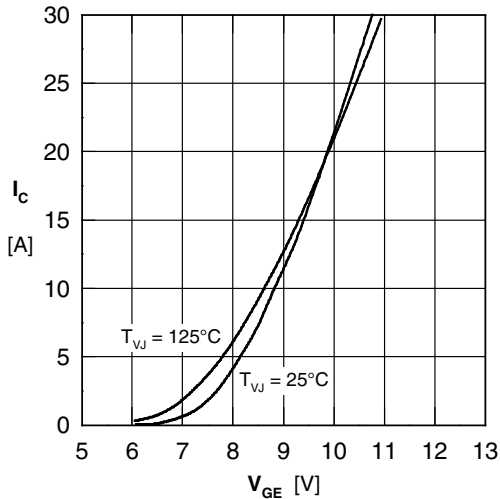


Fig. 3 Typ. transfer characteristics

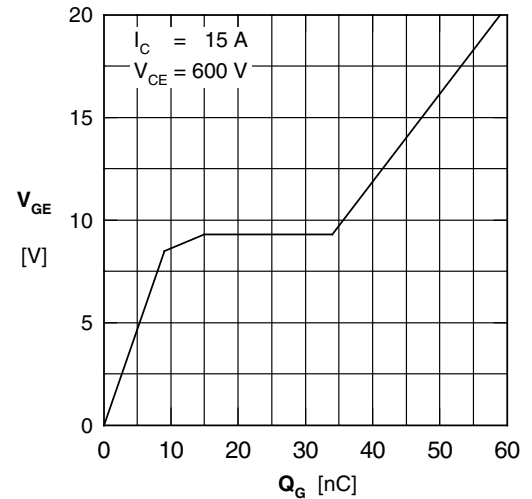


Fig. 4 Typ. turn-on gate charge

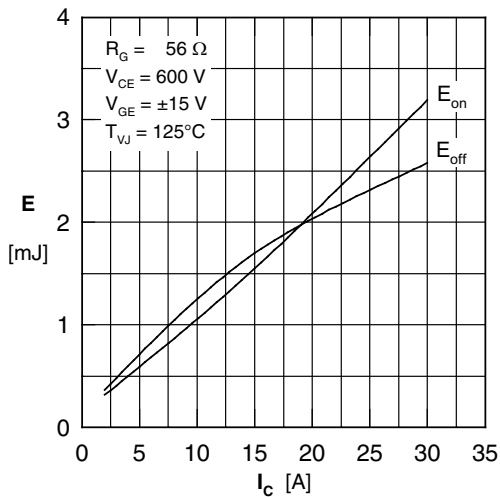


Fig. 5 Typ. switching energy vs. collector current

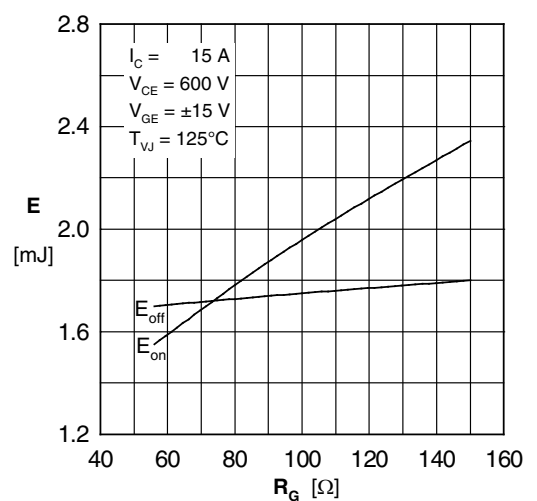


Fig. 6 Typ. switching energy vs. gate resistance

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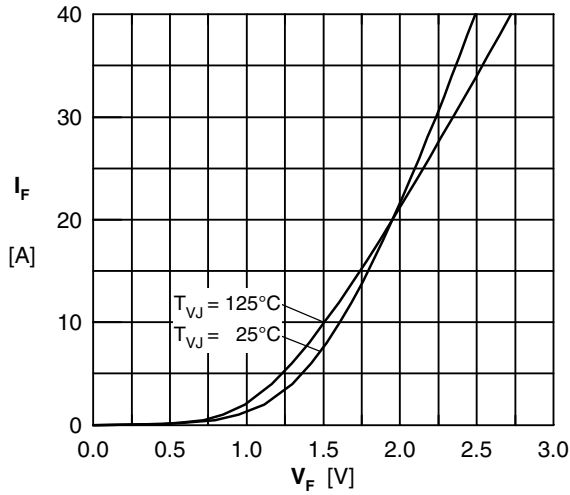


Fig. 7 Typ. Forward current versus  $V_F$

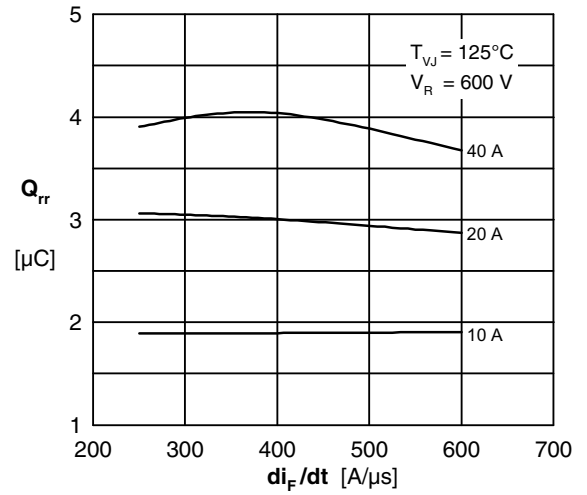


Fig. 8 Typ. reverse recov.charge  $Q_{rr}$  vs.  $di/dt$

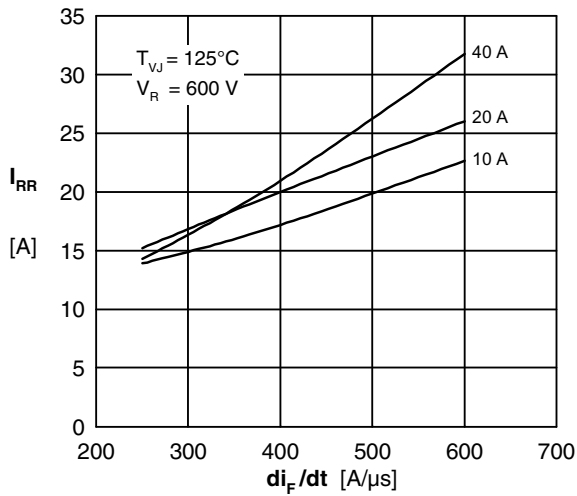


Fig. 9 Typ. peak reverse current  $I_{RRM}$  vs.  $di/dt$

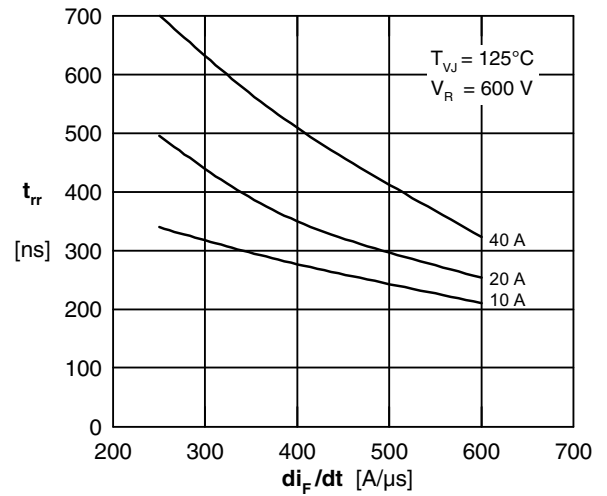


Fig. 10 Typ. recovery time  $t_{rr}$  versus  $di/dt$

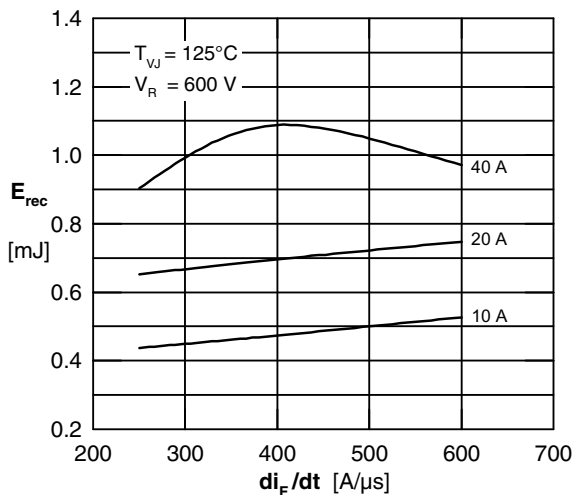


Fig. 11 Typ. recovery energy  $E_{rec}$  versus  $di/dt$

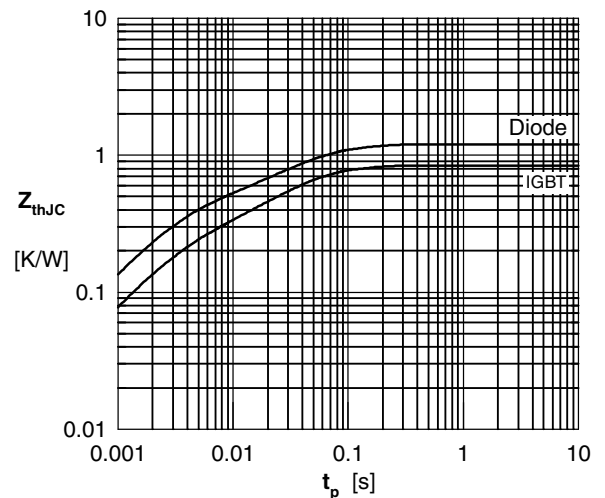


Fig. 12 Typ. transient thermal impedance